

ABSTRACT

With the invention, it is possible to avoid deterioration in short-channel characteristics, caused by a silicon germanium layer coming into contact with the channel of a strained SOI transistor. Further, it is possible to fabricate a double-gate type of strained SOI transistor or to implement mixedly mounting the strained SOI transistor and a conventional silicon or SOI transistor on the same wafer. According to the invention, for example, a strained silicon layer is grown on a strain-relaxed silicon germanium layer, and subsequently, portions of the silicon germanium layer are removed, thereby constituting a channel layer in the strained silicon layer.